

**JOANNEUM RESEARCH Forschungsgesellschaft
Institute MATERIALS, Weiz, Austria**

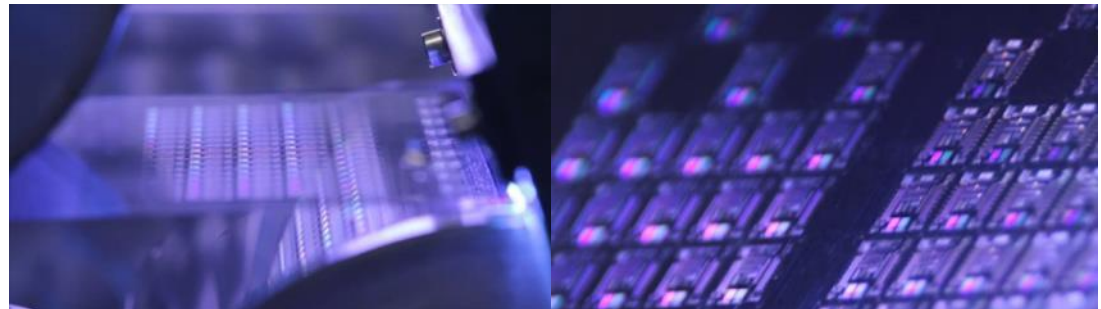
„Large-area patterning by roller-based nanoimprint lithography“

Ursula Palfinger, Dieter Nees, Stephan Ruttloff,
Markus Leitgeb, Maria Beleggratis, Barbara Stadlober

Outline

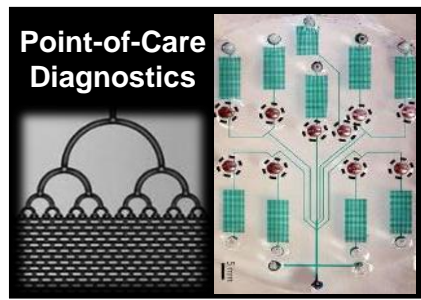
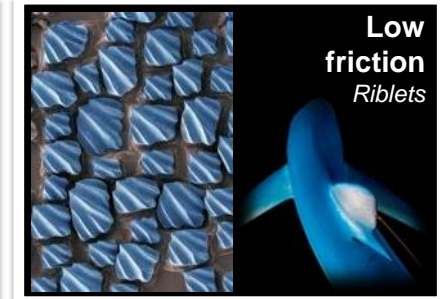
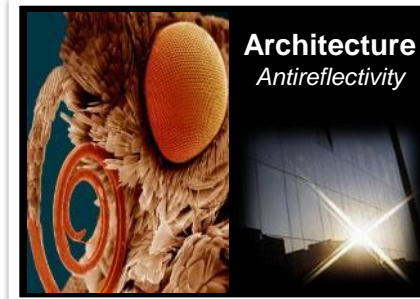
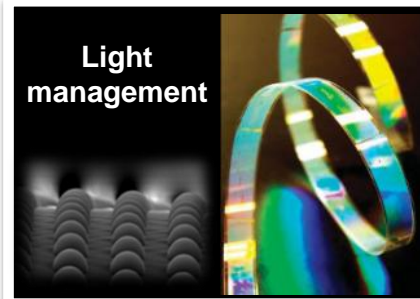
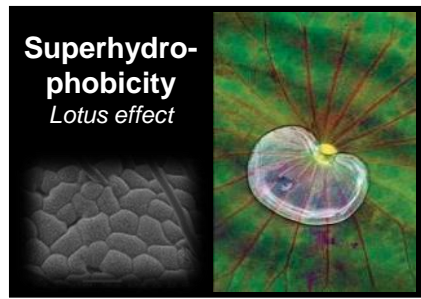
2

- **Motivation** – Small structures on large areas
- **Technology** – Roll-to-roll Nanoimprinting (R2R NIL)
 - Processes
 - Machinery
- **Materials** – Prerequisites for residual-free imprinting
- **Applications** – Roller-based fabrication of highly resolved metal patterns by a combination of residual-free NIL and a subsequent lift-off for transparent conductive foils and product ID features
- **Summary**

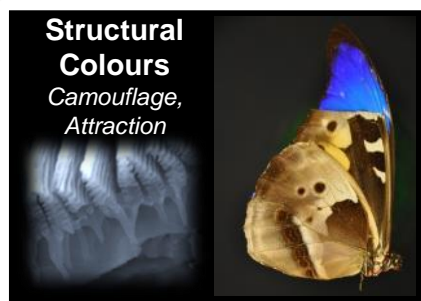
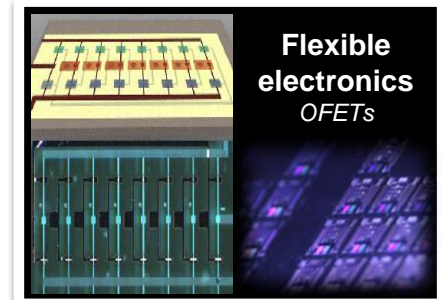


Small structures on large areas

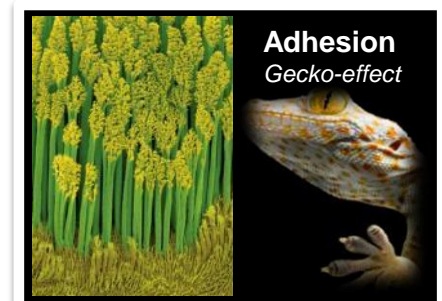
3



Where is highly resolved patterning on large areas interesting?

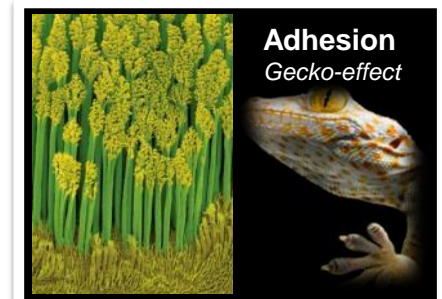
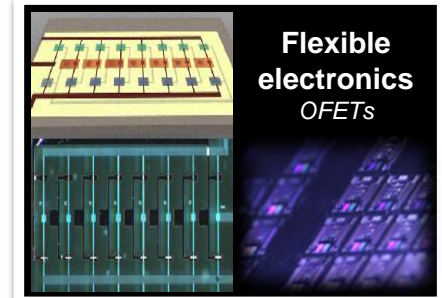
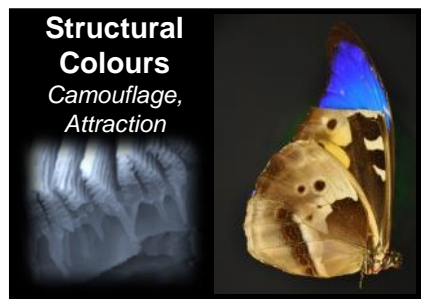
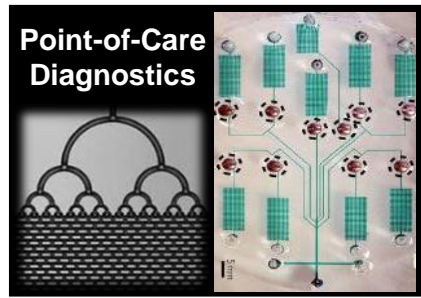
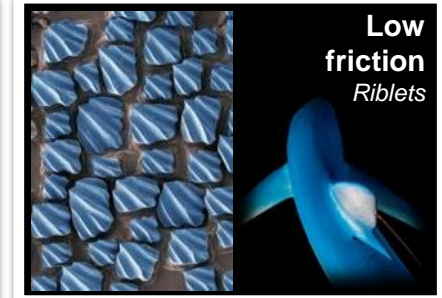
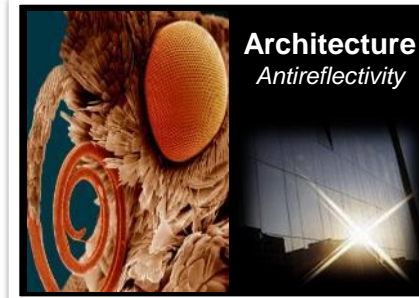
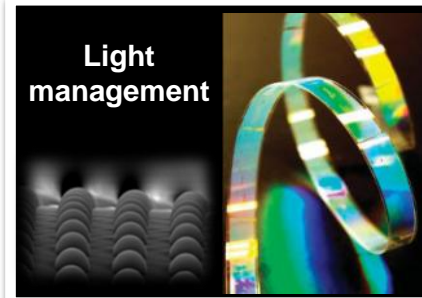
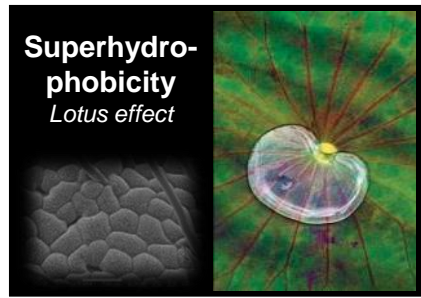


Others:
Transport
Traffic
Security
Packaging
Energy Harvesting
...



Small structures on large areas

4



How can we produce them?

- 1) micro and nano
- 2) 2D – 2.5D
- 3) large flexible areas
- 4) industrial process

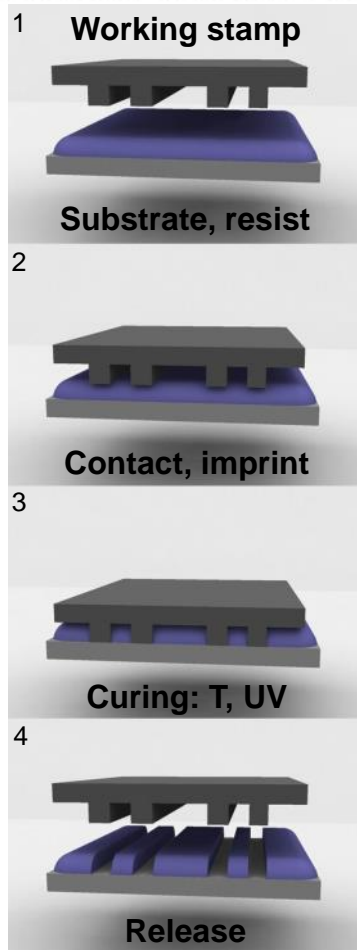
5

Nanoimprint lithography

Fast + accurate method for structure transfer

UV or thermal curing of resist

Very versatile (geometries, structure size)



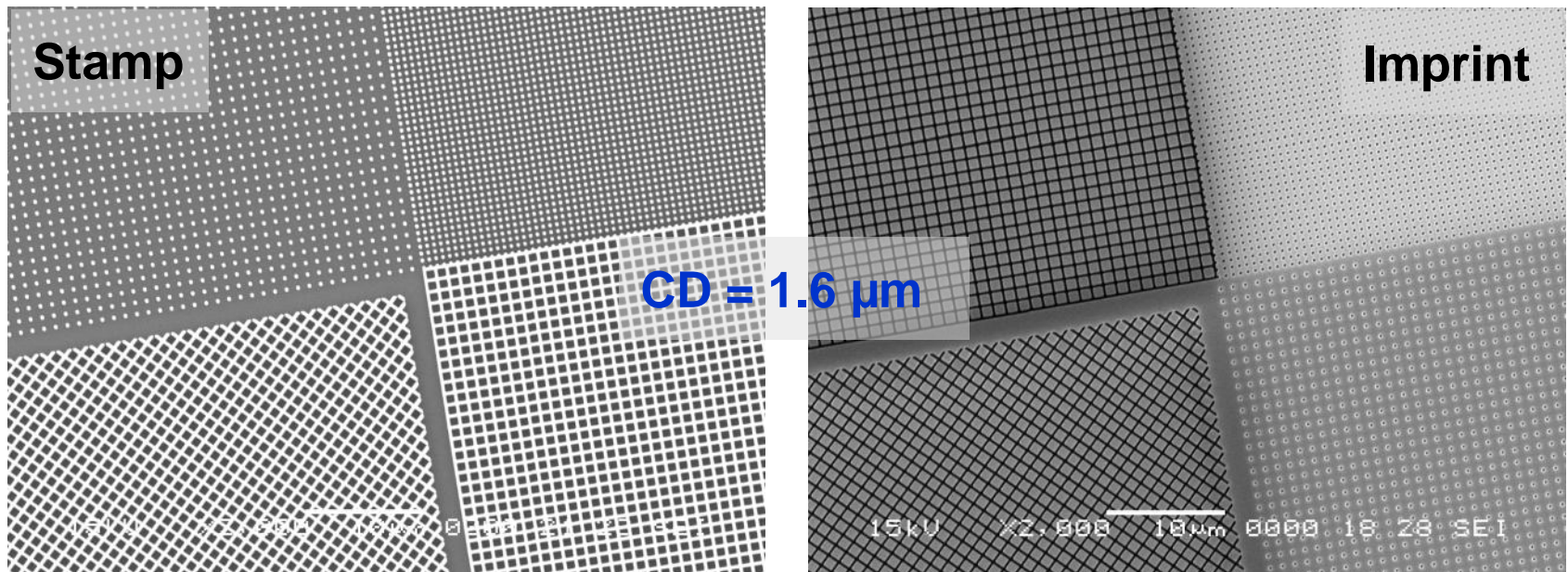
6

Nanoimprint lithography

Fast + accurate method for structure transfer

UV or thermal curing of resist

Very versatile (geometries, structure size)



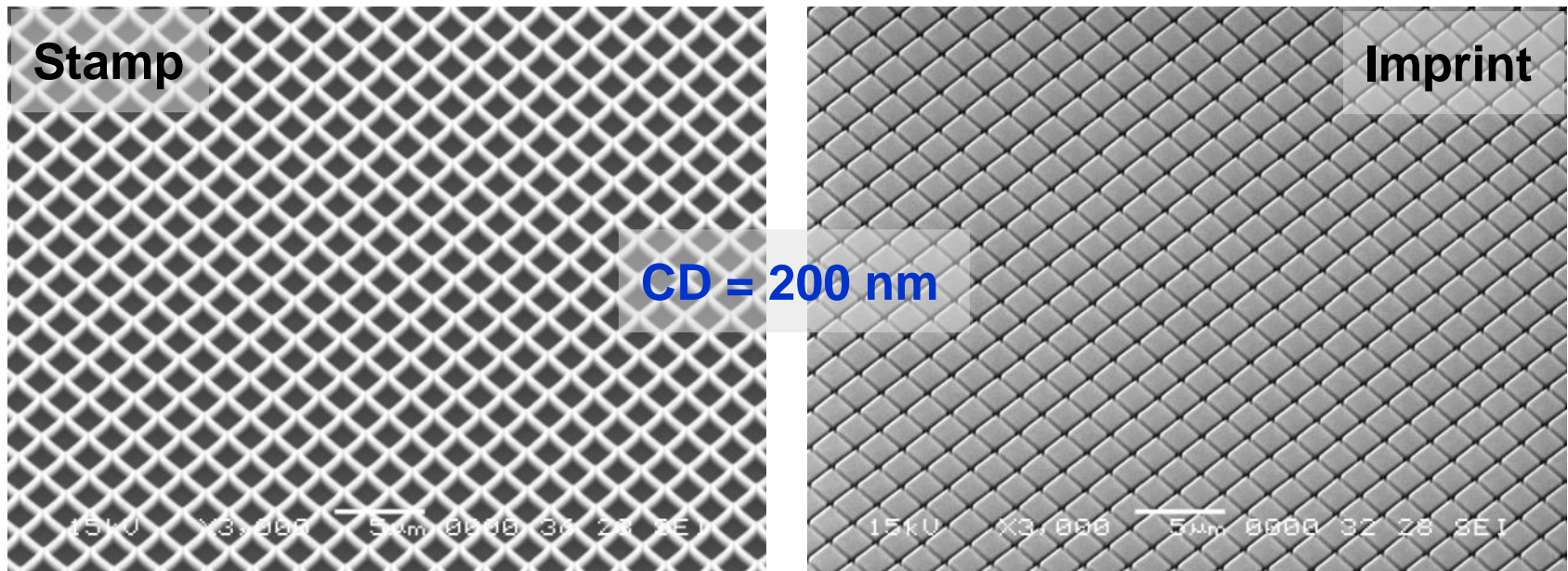
7

Nanoimprint lithography

Fast + accurate method for structure transfer

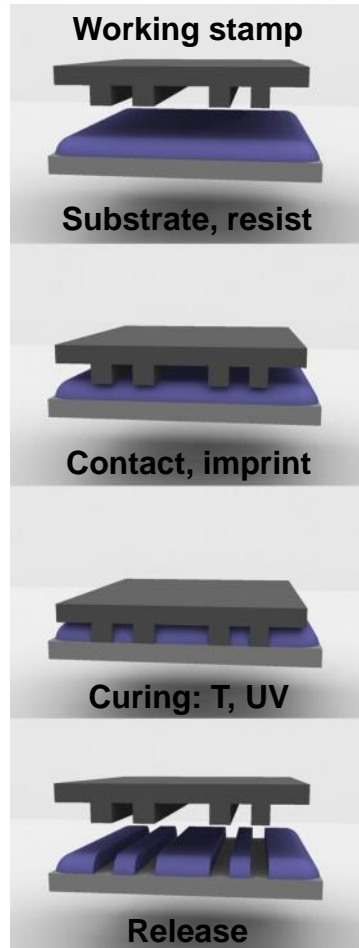
UV or thermal curing of resist

Very versatile (geometries, structure size)



8

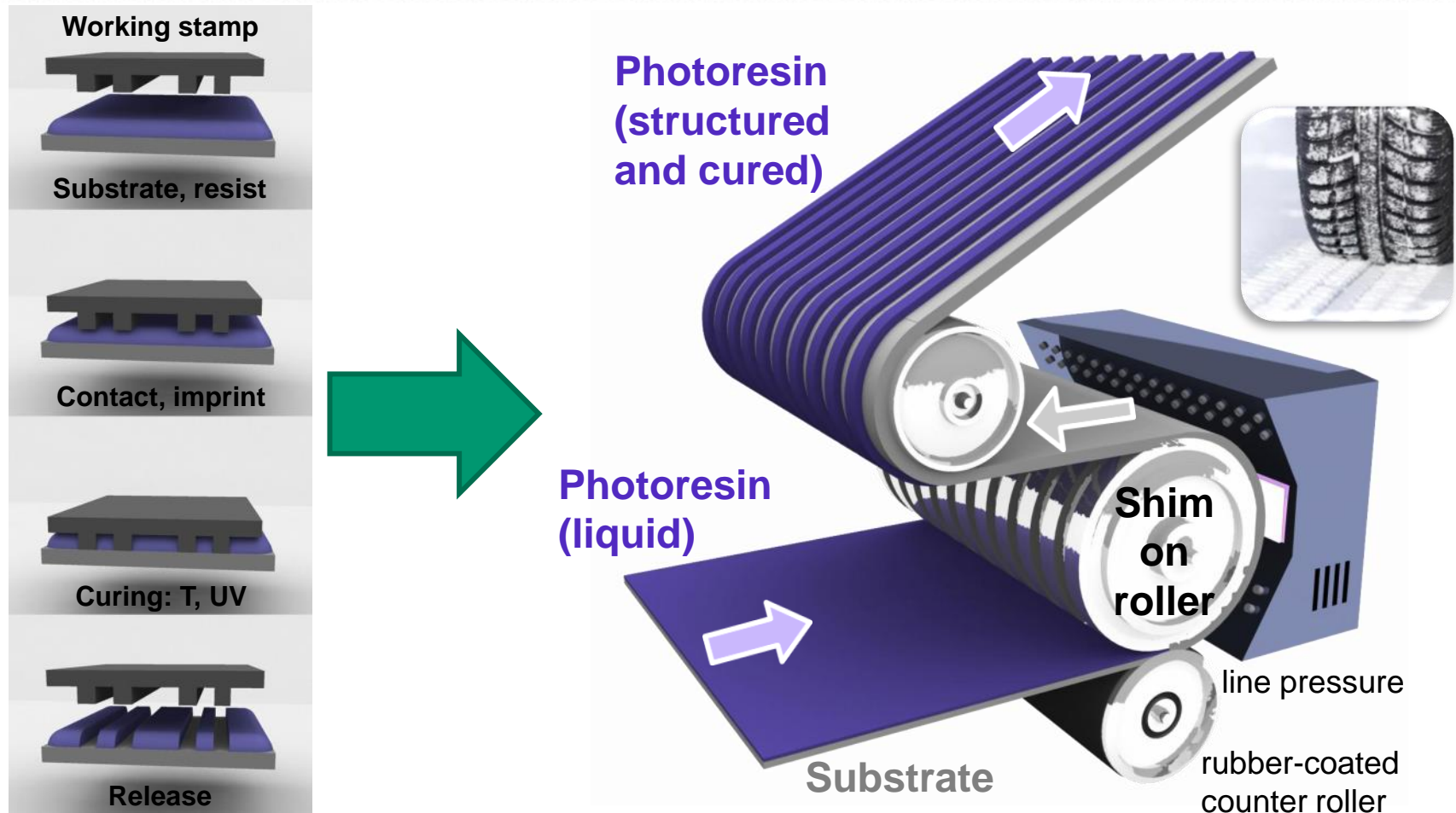
Nanoimprint lithography



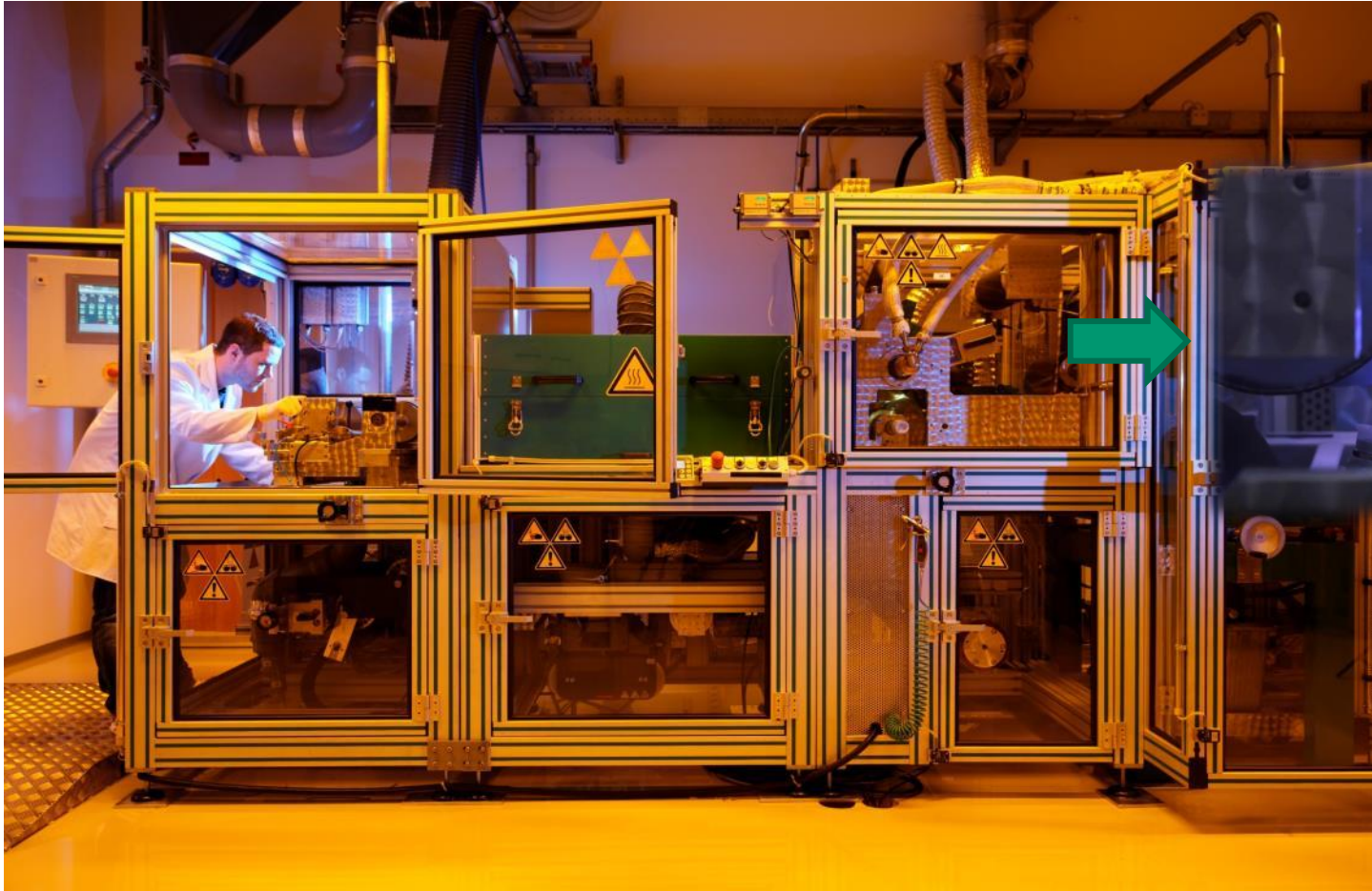
Critical issues – Batch NIL (serial)

- Master (pattern quality, roughness)
- Control of adhesion between master and resist
- Resist viscosity (filling)
- Curing behavior (fast, low shrinkage)
- Fabrication volumes and process time
- Upscaling?

Roll-to-Roll Nanoimprint lithography



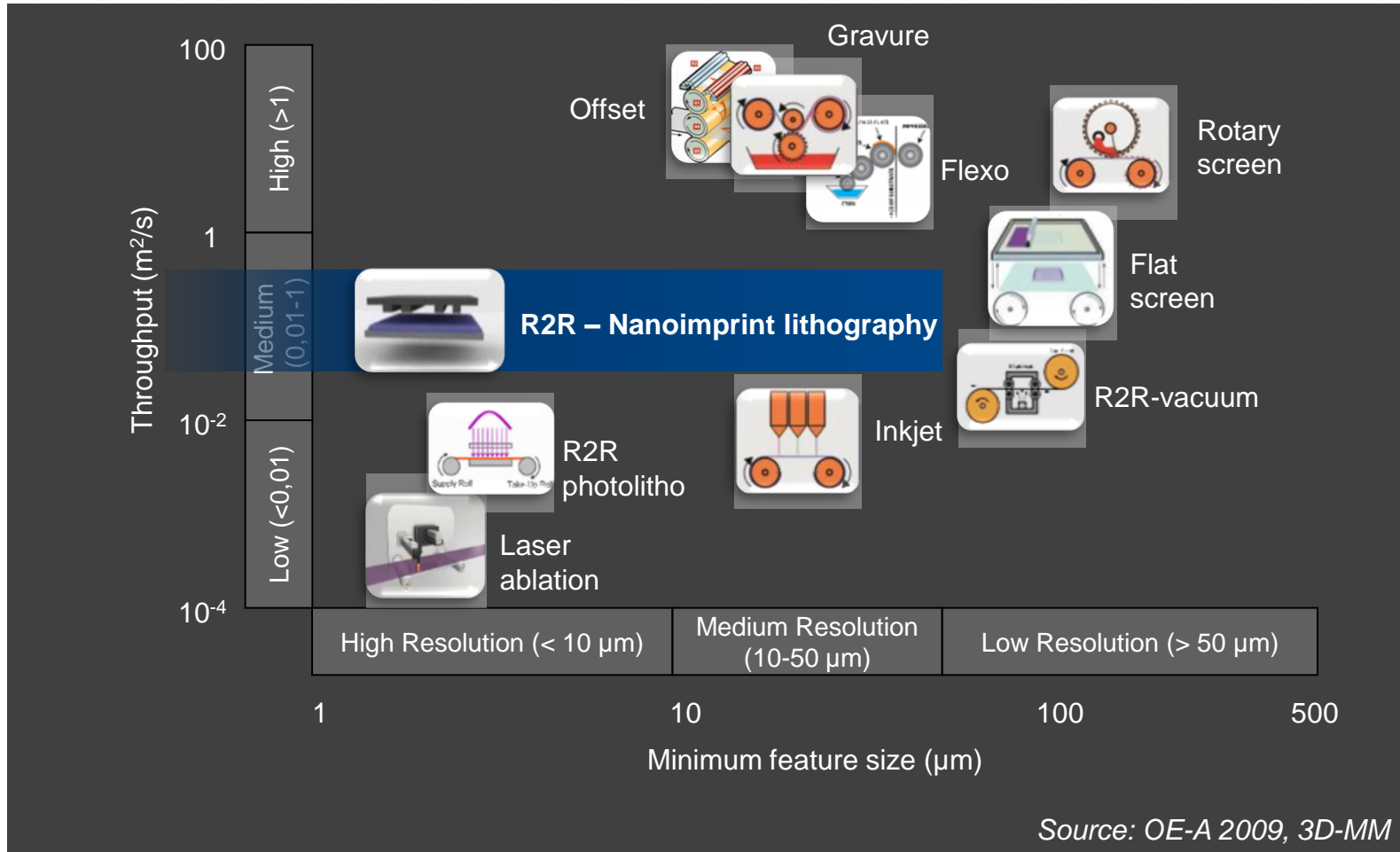
Roll-to-Roll Nanoimprint lithography



Max. web width = 250 mm
Web speed = 0.5 – 30 m/min
Max. UV intensity = 200 W/cm
Line pressure UV-NIL = 18 kN
Line pressure HE = 100 kN

Resolution and throughput of printing technologies

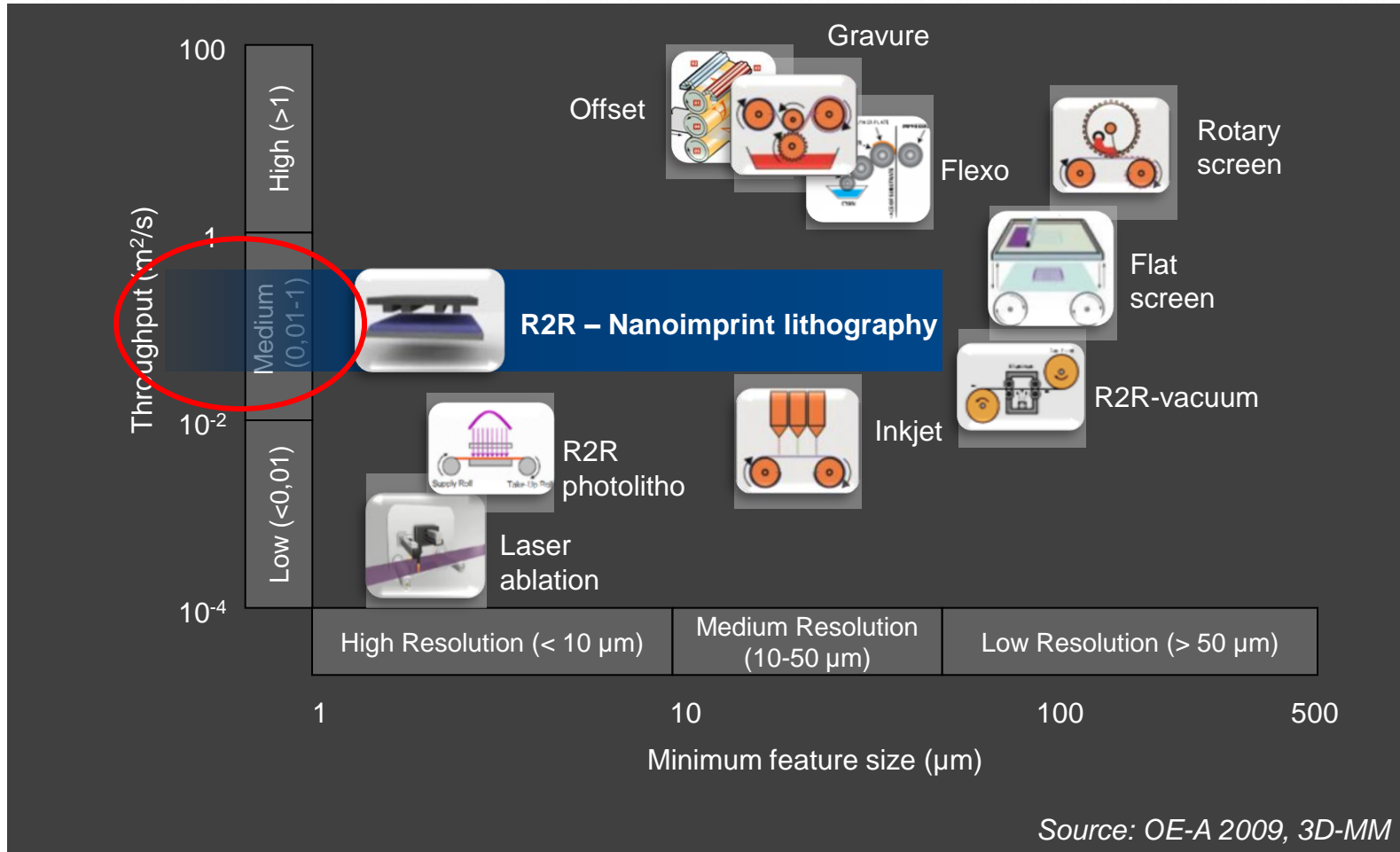
11



Source: OE-A 2009, 3D-MM

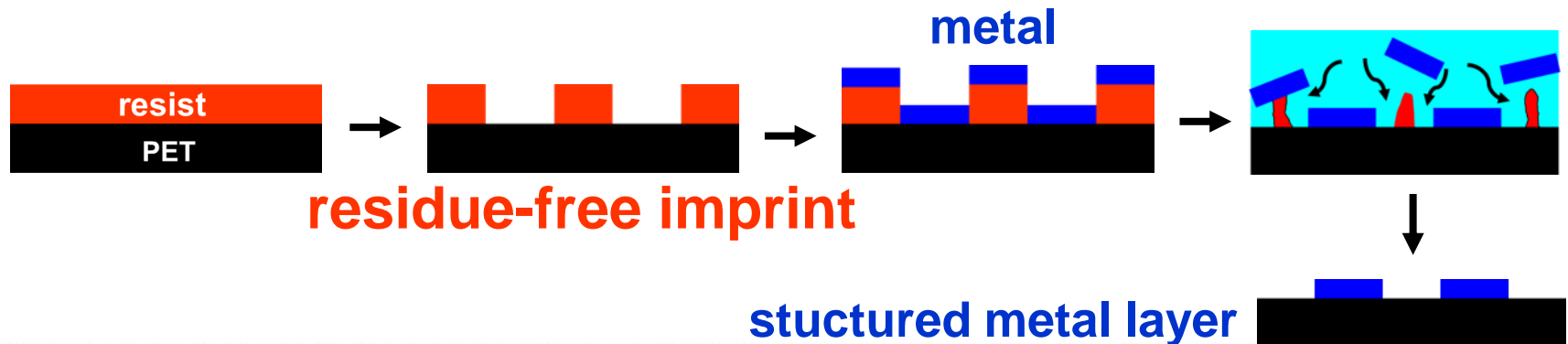
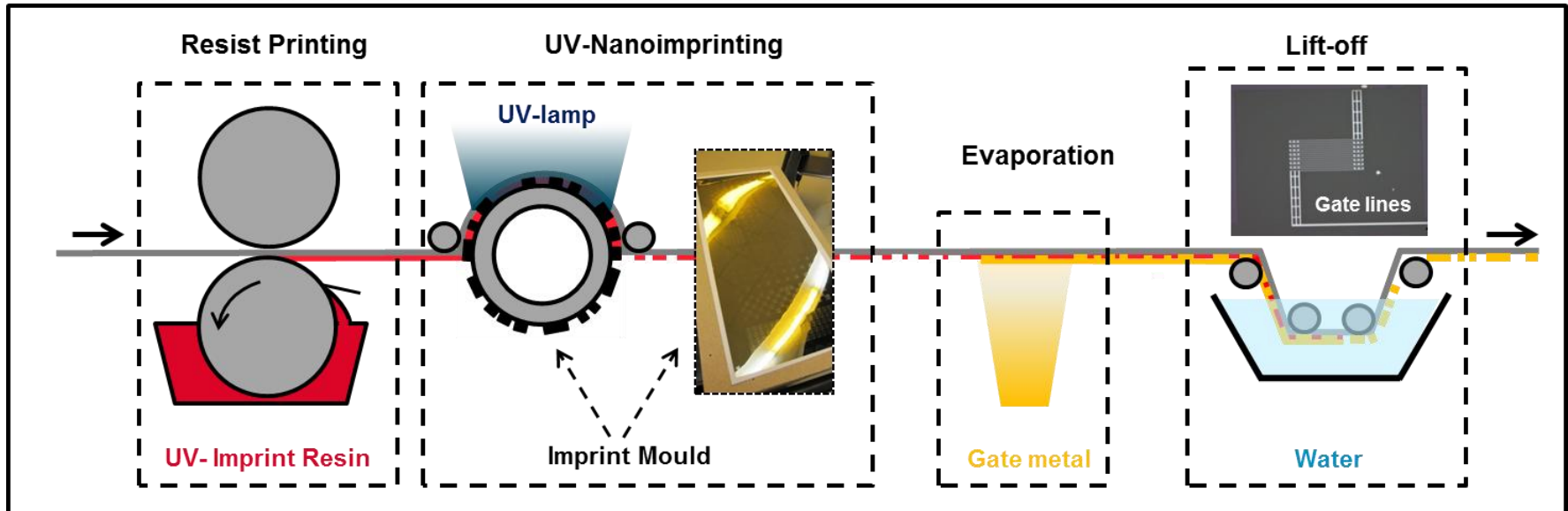
Resolution and throughput of printing technologies

12



Creation of highly resolved metal patterns in R2R environment

13

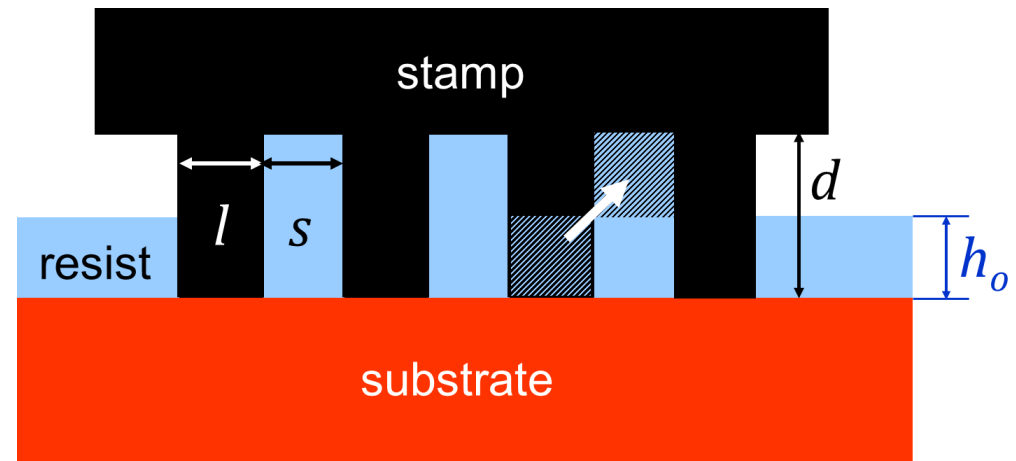
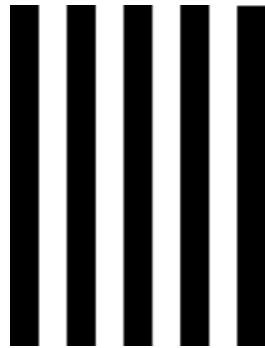


Critical for residual-free imprint: PATTERN GEOMETRY

14



Structure depth and resist thickness



l : line width

s : space width

d : structure depth

h_o : initial resist film thickness

$$\frac{d}{h_o} > \left(1 + \frac{l}{s} \right)$$

for open patterns

Critical for residual-free imprint: RESIST FLOW BEHAVIOR

15

Squeeze flow model

“Stefan’s equation”:

$$t = \frac{\eta l^2}{2p} \left(\frac{1}{h_r^2} - \frac{1}{h_o^2} \right)$$

t : imprint time

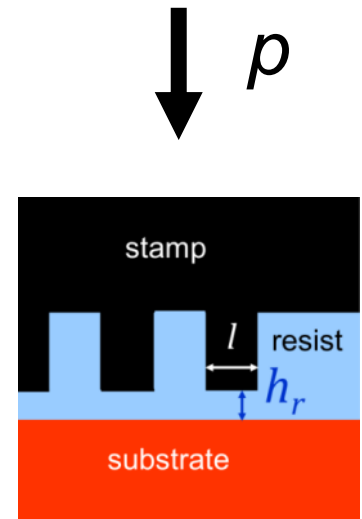
η : resist viscosity

l : imprinted line width

p : imprint pressure

h_r : residual resist film thickness

h_o : initial resist layer thickness



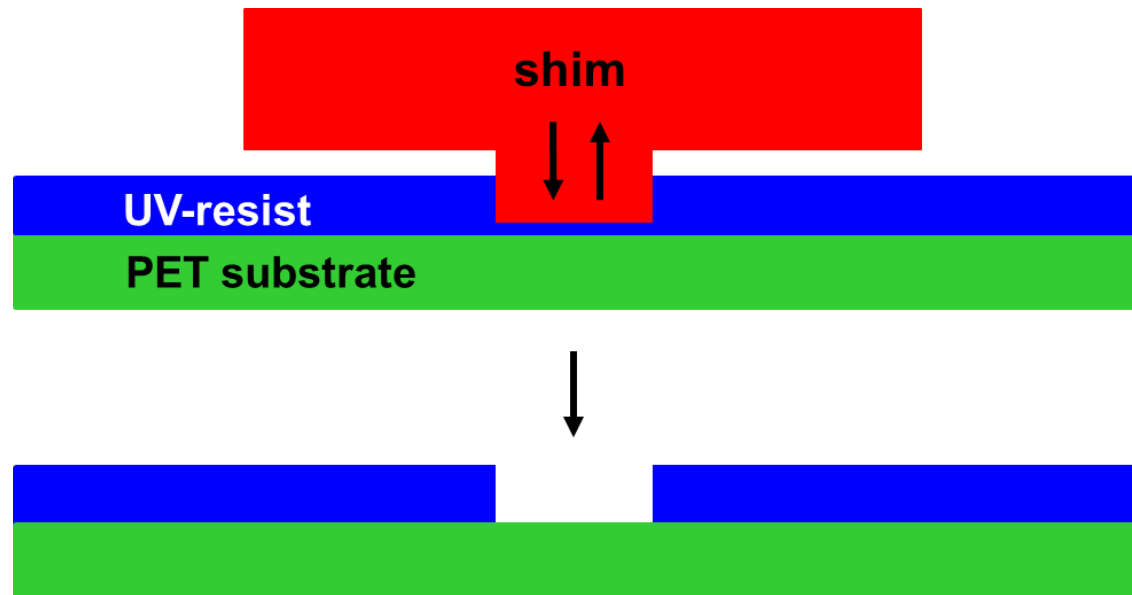
*For vanishing residual resist film thickness
the imprint time approaches infinity ...*

Critical for residual-free imprint: SURFACES VS. RESIST CHEMISTRY

16

Spontaneous dewetting and balance of interfacial forces

$$S = \gamma_{\text{Substrate/Shim}} - (\gamma_{\text{Substrate/Resin}} + \gamma_{\text{Resin/Shim}}) < 0$$



γ_{XY} : interfacial energy

S: spreading coefficient

Critical for residual-free imprint: CHOICE OF RESIST

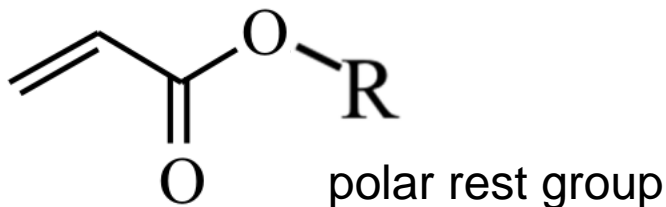
17

UV-NIL resist for aqueous lift-off

Monomer

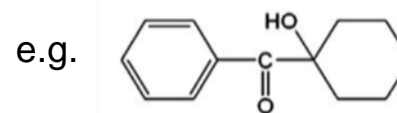
- low viscosity
- water soluble
- monofunctional

Acrylate

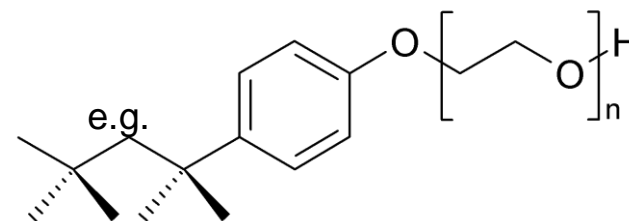


$$\eta = 10 \text{ mPas}$$

Photoinitiator



Non-ionic surfactant

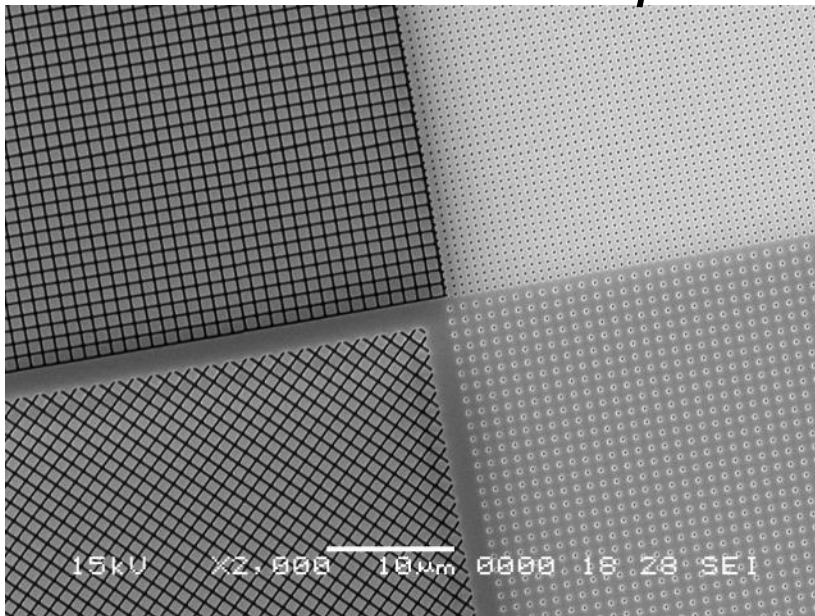


Tuning of interfacial energies

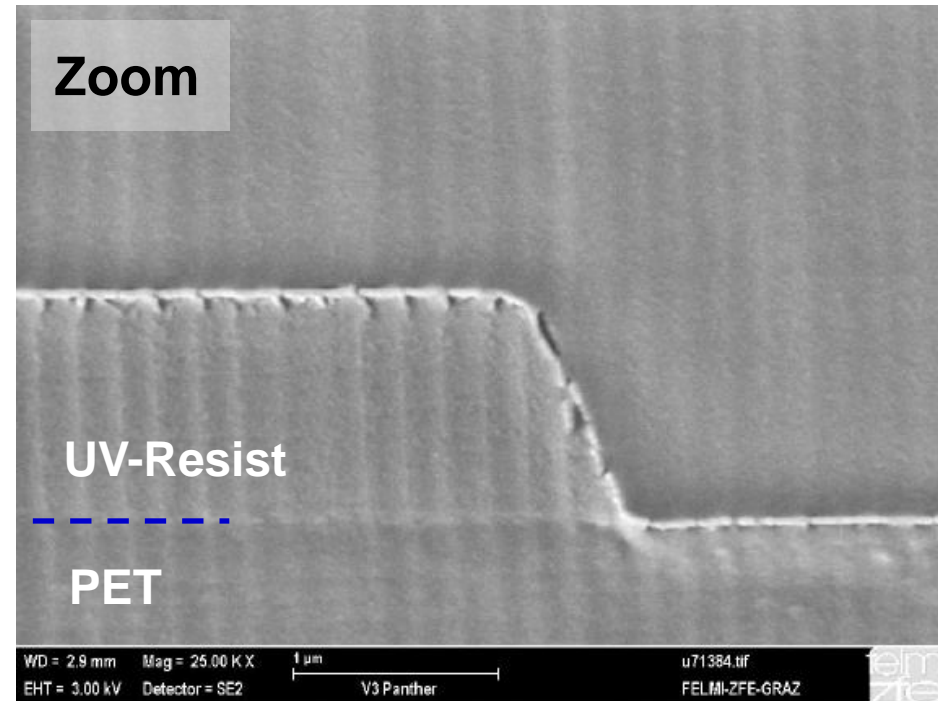
$$20 \text{ mN/m} < \gamma < 45 \text{ mN/m}$$

Residual-free R2R imprint

SEM: top view

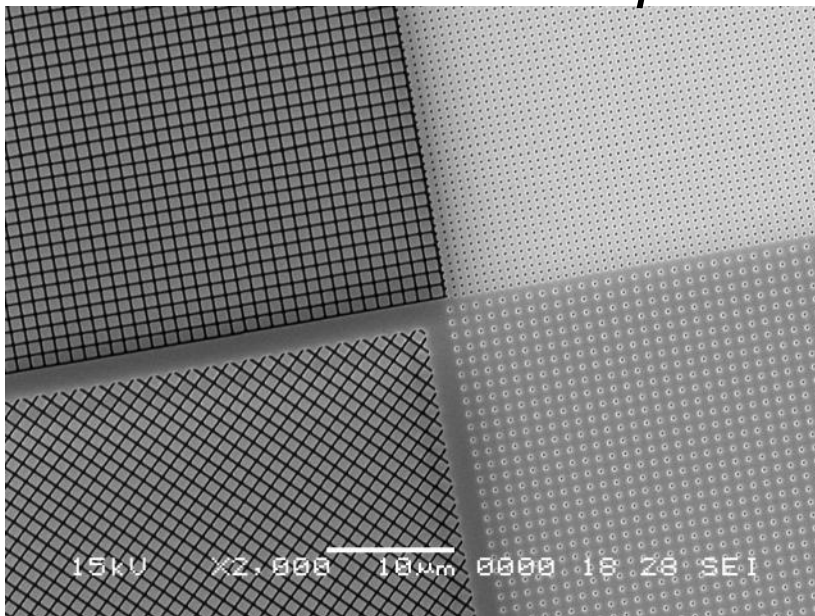


SEM: cross section

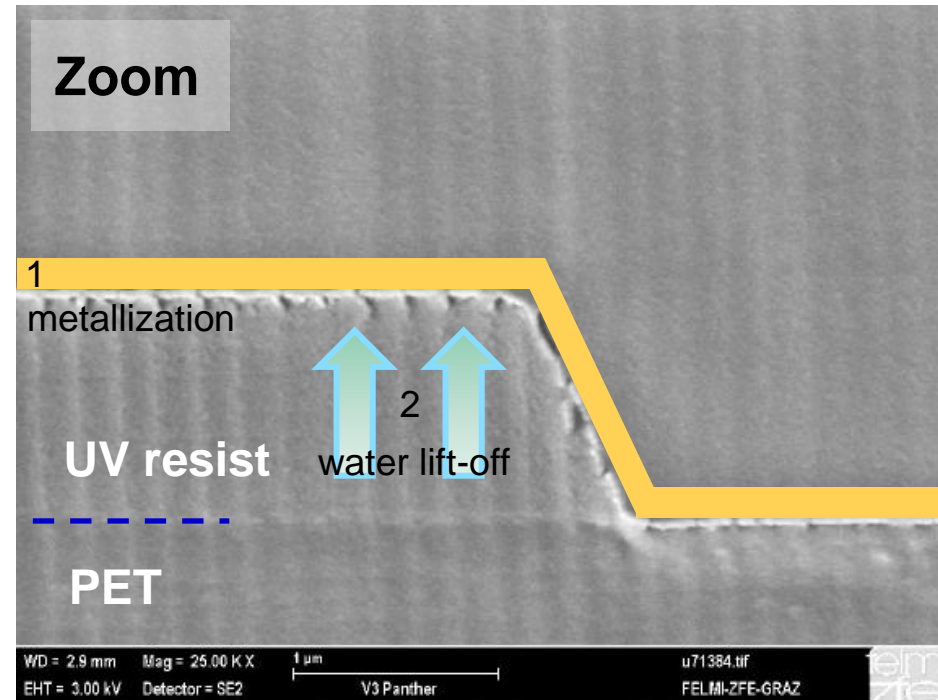


Residual-free R2R imprint

SEM: top view



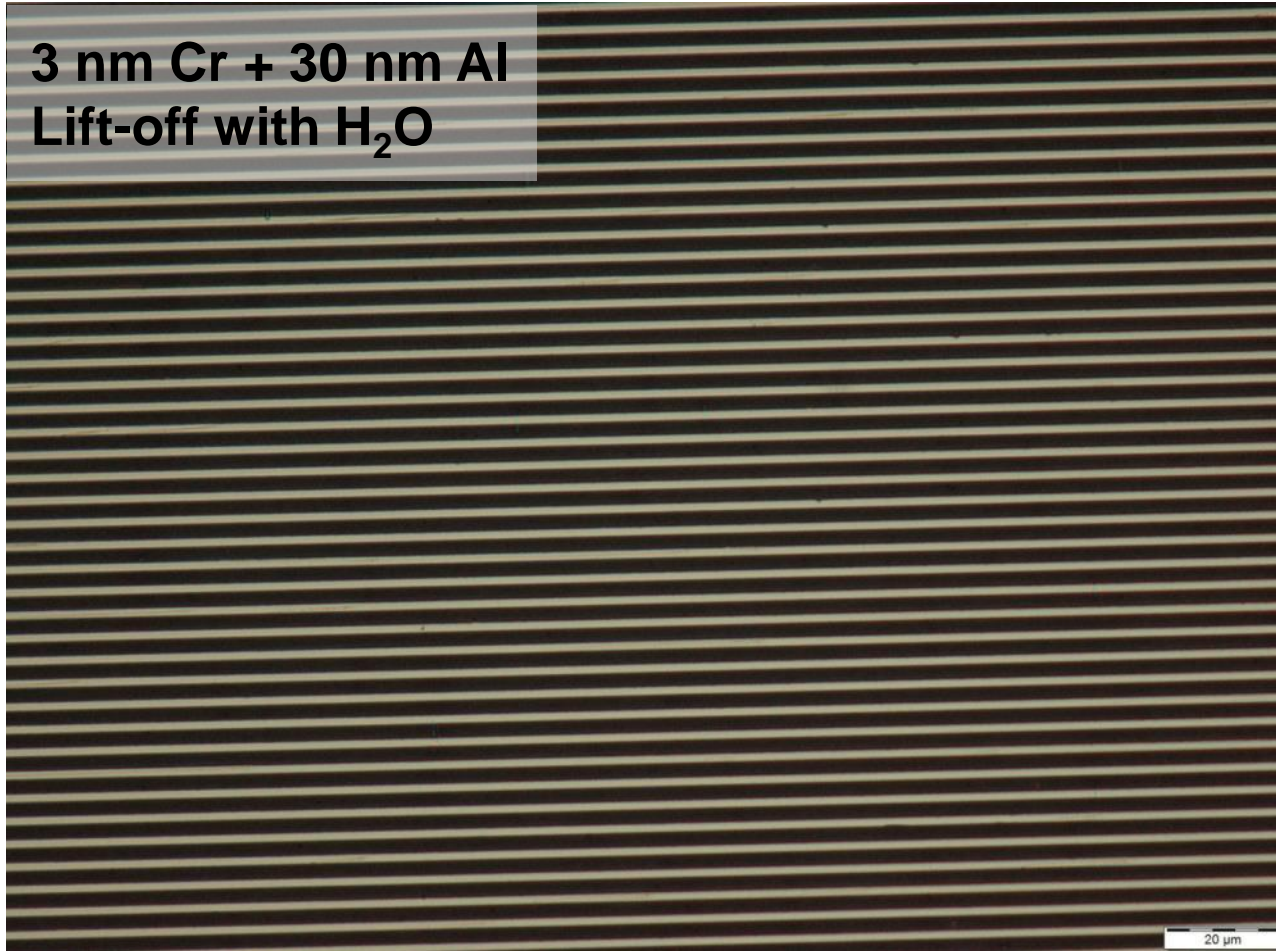
SEM: cross section



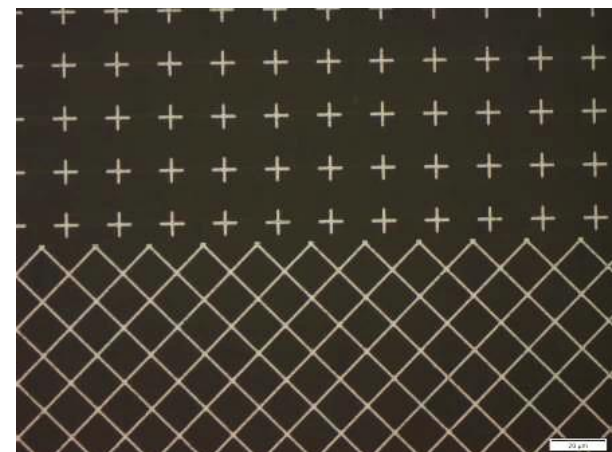
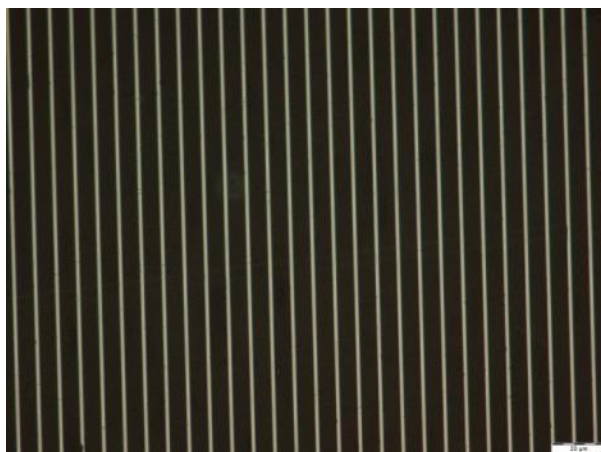
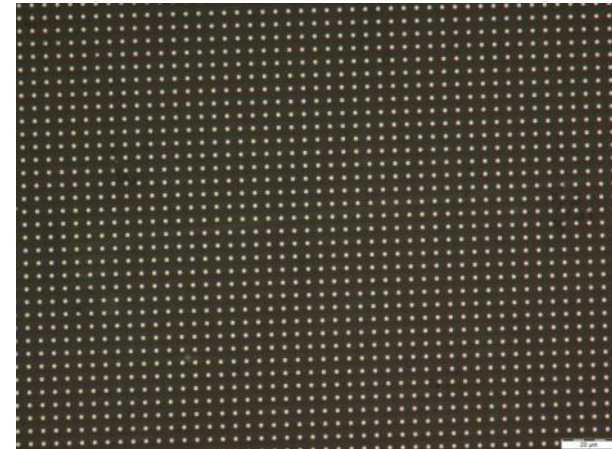
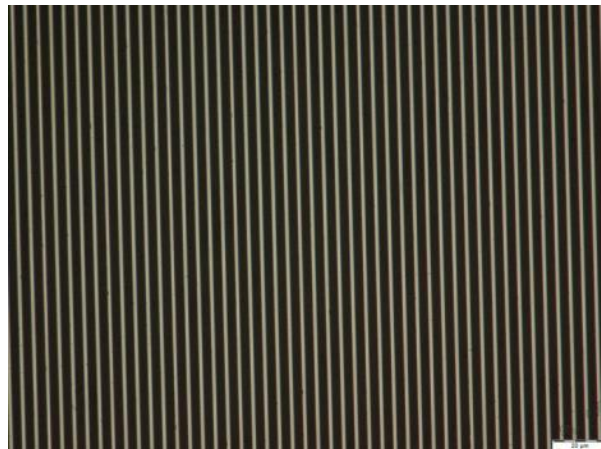
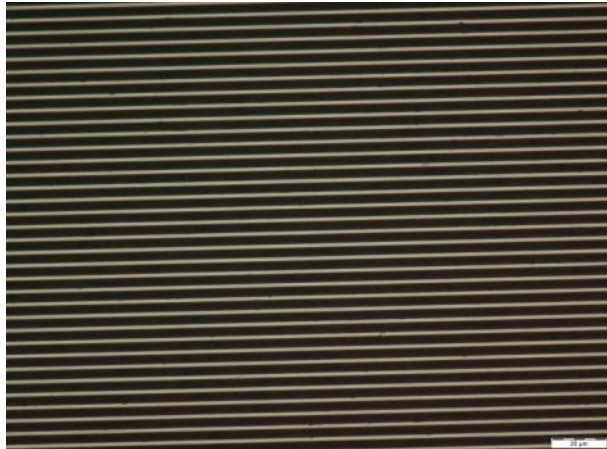
20

Al lines, CD = 1.6 μm

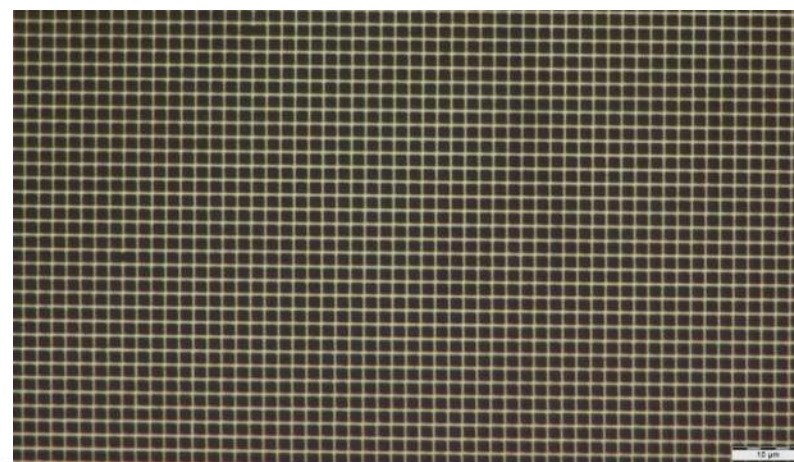
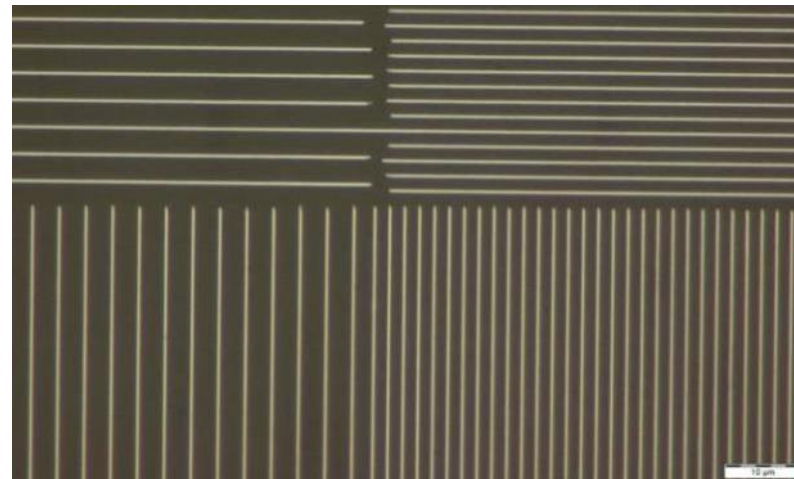
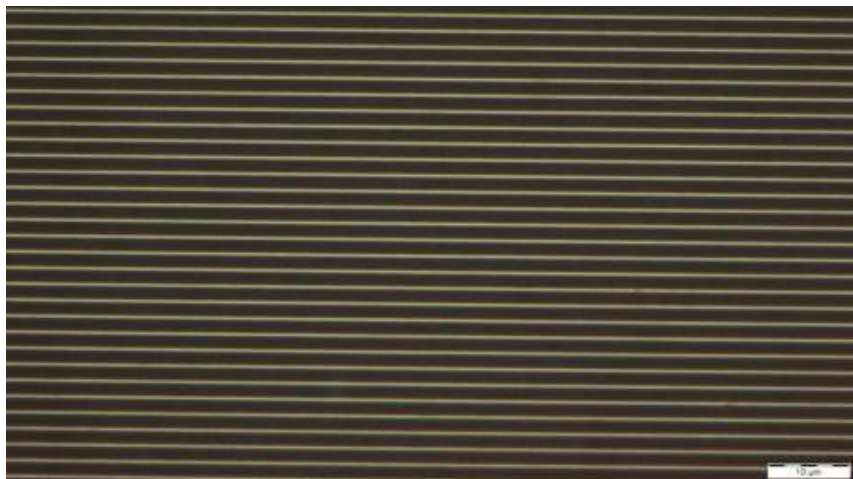
**3 nm Cr + 30 nm Al
Lift-off with H₂O**



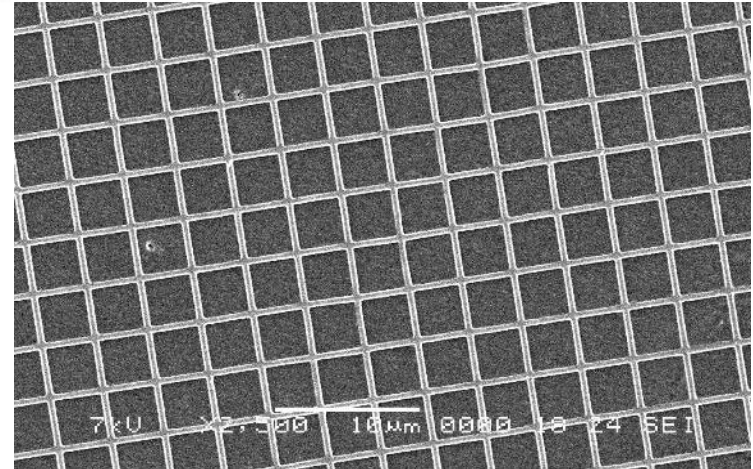
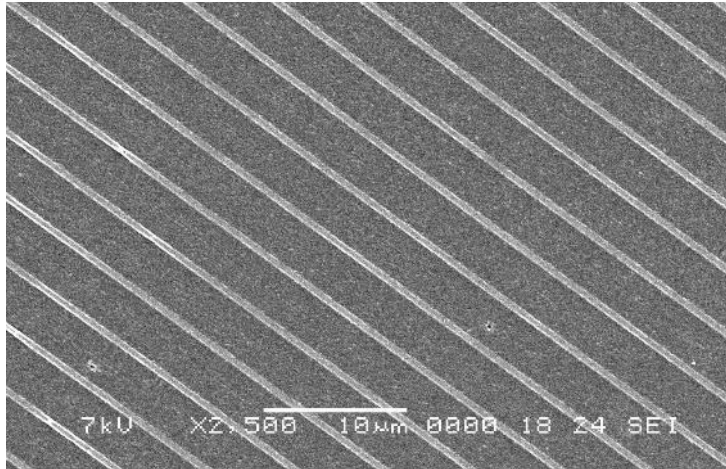
Al patterns, CD = 1.6 μm



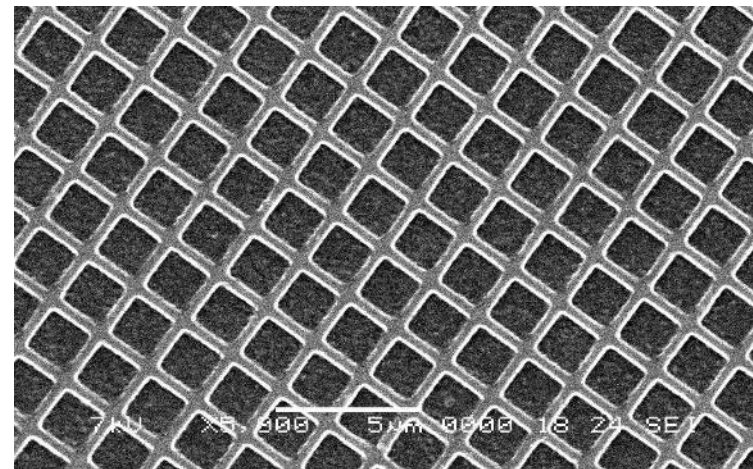
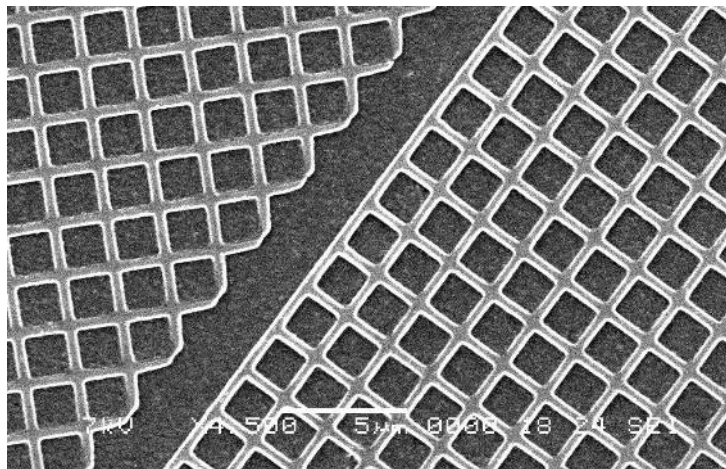
Al patterns, CD = 400 nm



Application “nano”: Metal grids for transparent conductive foils



SEM
400 nm



Application “nano”: Metal grids for transparent conductive foils



Source: PolyIC



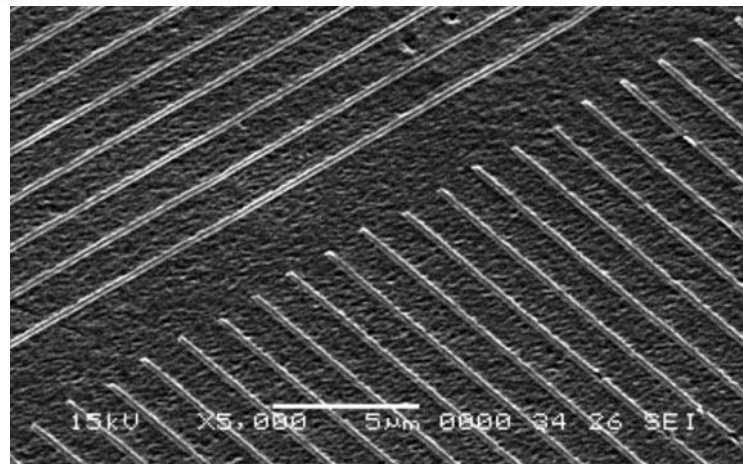
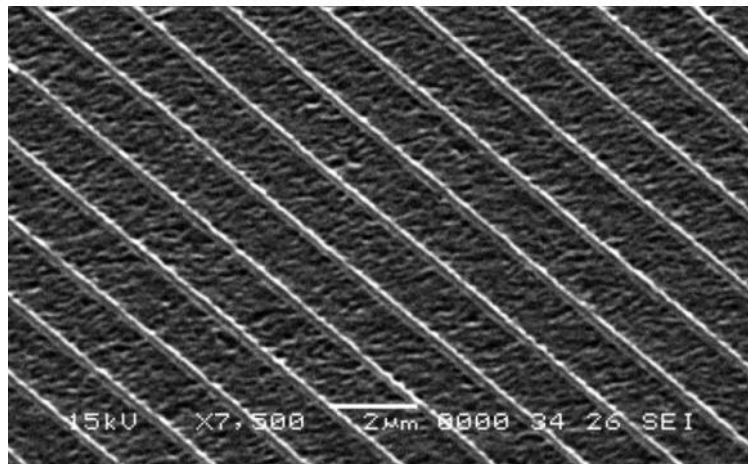
Source: Samsung



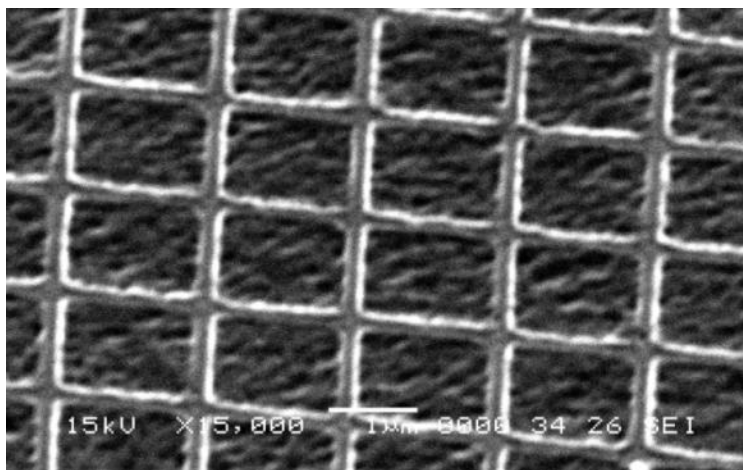
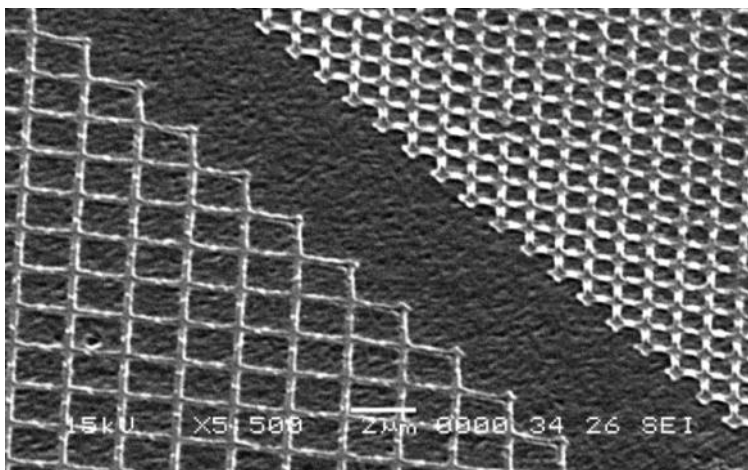
PyzoFlex technology

Flexible displays, touch panels, sensor surfaces, shielding foils,...

Application “nano”: Metal grids for transparent conductive foils



SEM
200 nm



Summary

26

- Roller-based nanoimprinting is a large area, high resolution patterning process with very high potential.
- Residue-layer free R2R UV-NIL is possible, when pattern geometries and stamp and resin surface chemistry is optimized.
- We developed an acrylate-based imprint resin for water-based lift-off and used it for highly-resolved metal patterning on foil without the need of etching.
- Applications can be seen in electronics, optics, sensing, security features..., shown examples: transparent conducting, packaging

Acknowledgements



*Dieter Nees
Markus Leitgeb*



Herbert Gold



Stephan Ruttloff



*Laco Kuna
Volker Schmidt*



Maria Beleggratis



Barbara Stadlober



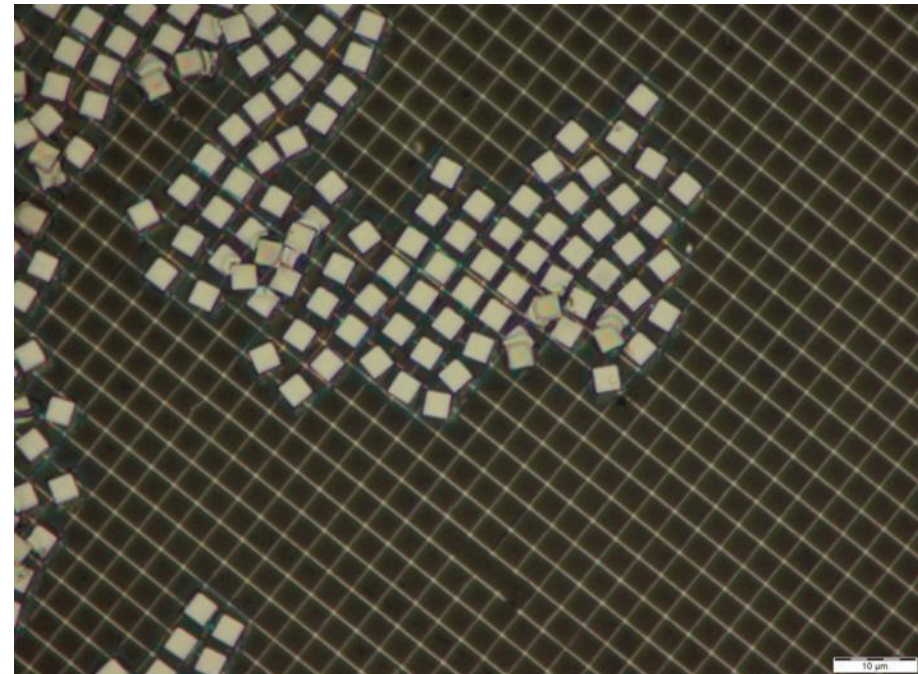
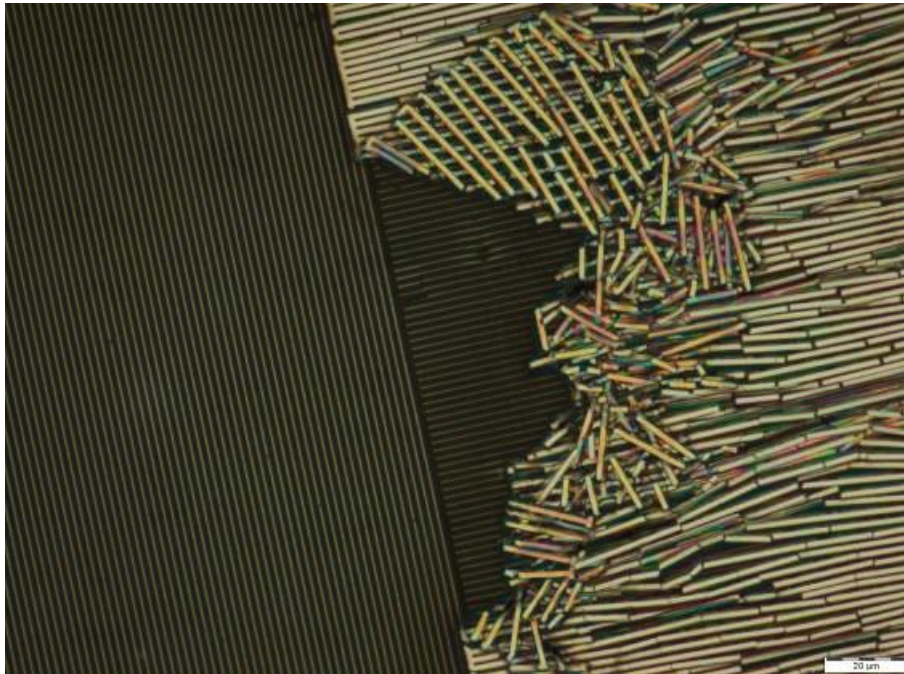
FFG
FORSCHUNG WIRKT.

bmwfw
Bundesministerium für
Wissenschaft, Forschung und Wirtschaft

bmwfi



Lift-off in progress



Thank you for your interest!